Auxiliary field strengths below Hx<1.5 kA/m are not recommended, as small disturbances may flip the magnetization domains. Sometimes, the magnetic conditions in the application may provide enough Hx bias field stabilization. MEAS Germany can provide advice for customer specific magnet arrangements.

If a bias field Hx is not applied or Hx is less than 2.5 kA/m, the sensor may be used only in a limited field range Hy, depending on the present total bias field Hx,tot. In this case, it is strongly recommended to 'premagnetize' the sensor, i.e. align all magnetic domains consistently, prior to the measurement.

Hx,tot is the sum of all acting magnetic fields in x direction at the sensor die.

Do not use the sensor outside the safe operating area. Leaving the save operating area can destroy an existing premagnetization and therefore will lead to unreproducible sensor signals.

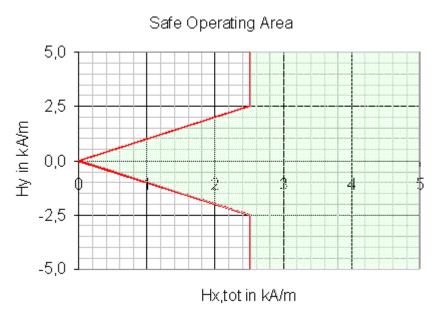


Figure 2: Safe operating area

CHARACTERISTIC VALUES / SENSOR SPECIFICATIONS

Parameter	Symbol	Condition	Min	Тур	Мах	Unit
Operating Limits	1					
max. supply voltage	$V_{cc,max}$				10	V
max. current	I _{cc,max}				9	mA
operating temperature	T _{op}		-40		+150	°C
storage temperature	T _{st}		-40		+150	°C
General Sensor Specific	ations					
TC of amplitude	TCSV	Condition A, C		-0.35		%/K
TC of resistance	TCBR	Condition A, C		+0.35		%/K
TC of offset	TCVoff	Condition A, C	-4	0	+4	μV/V/K
Sensor Specifications K	MY 20 S, KM	Z 20 S, KMY 22 (T=25 °	C, Hx=3 kA/m e	xternally)		
Supply voltage	V _{cc}	Condition A, B		5		V
Bridge resistance	R₀	Condition A, B	1200	1700	2200	Ω
Output signal range	$\Delta V_0/V_{cc}$	Condition A, B	16	20	24	mV/V
Offset voltage	$V_{\text{off}}/V_{\text{cc}}$	Condition A, B	-1	0	+1	mV/V
Sensitivity	S	Condition A, B	3.7	4.7	5.7	mV/V/kA/m

Hysteresis	V_{H}/V_{cc}	Condition A, B	-	-	50	μV/V
Sensor Specifications k	(MY 20 M, KM	Z 20 M (T=25 °C, Hx=1.	.5±0.5 kA/m inte	ernally)		
Supply voltage	V _{cc}	Condition A, B		5		V
Bridge resistance	Rb	Condition A, B	1200	1700	2200	Ω
Output signal range	$\Delta V_0/V_{cc}$	Condition A, B	16	20	24	mV/V
Offset voltage	V _{off} /V _{cc}	Condition A, B	-1.5	0	+1.5	mV/V
Sensitivity	S	Condition A, B	4	5.5	7	mV/V/kA/m
Hysteresis	V _H /V _{cc}	Condition A, B	-	-	50	μV/V
Sensor Specifications K	(MY 21 M (T=	25 °C, Hx=2.5±1.0 kA/m	internally)			
Supply voltage	V _{cc}	Condition A, B		5		V
Bridge resistance	Rb	Condition A, B	1100	1500	1900	Ω
Output signal range	$\Delta V_0/V_{cc}$	Condition A, B	8	9.5	12	mV/V
Offset voltage	V _{off} /V _{cc}	Condition A, B	48	50	52	%Vcc
Sensitivity	S	Condition A, B	2.05	2.50	3.10	mV/V/kA/m
Hysteresis	V _H /V _{cc}	Condition A, B	-	-	50	μV/V

Stress above one or more of the limiting values may cause permanent damage to the device. Exposure to limiting values for extended periods may affect device reliability.

MEASUREMENT CONDITIONS

Parameter	Symbol	Unit	Condition		
Condition A: Set Up Conditions					
Ambient temperature	Т	°C	23±5 Measurement results are extrapolated to 25°C by using the given temperature coefficients		
Supply voltage	V _{cc}	V	5		
Output voltage	Vo Vo/Vcc	mV mV/V	$V_{O}=(V_{0+} - V_{0-})$ Output voltages are also given independently on supply voltage: example: Vo/Vcc=(V_{0+} - V_{0-})/Vcc; measure MR half bridge against reference half bridge		
Reference half bridge			2* 2 kΩ 0.1% (KMY21M only)		
for full bridge sensors (KMY20S, KMY20M, KMY22, KMZ20S, KMZ20M)			for half bridge sensors (KMY 21 M)		